

ABSTRACT

An object of the present disclosure is to provide a sputtering target in which contamination of the sputtering target with a chlorine element as an impurity is suppressed and occurrence of abnormal discharge due to chlorine is suppressed in forming a thin film using the sputtering target to form a thin film having good orientation. The sputtering target according to the present disclosure is a sputtering target including aluminum and either a rare earth element or a titanium group element or both a rare earth element and a titanium group element, and the sputtering target has a chlorine content of 100 ppm or less.